

The RF Line
NPN Silicon
High-Frequency Transistor

... designed for thick and thin-film circuits using surface mount components and requiring low-noise, high-gain signal amplification at frequencies to 1.0 GHz.

- High Gain — $G_{pe} = 15$ dB Typ @ $f = 500$ MHz
- Low Noise — $NF = 2.4$ dB Typ @ $f = 500$ MHz
- Available in tape and reel packaging options by adding suffix:
T1 suffix = 3,000 units per reel
T3 suffix = 10,000 units per reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	15	Vdc
Collector-Base Voltage	V_{CBO}	20	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc
Collector Current — Continuous	I_C	35	mAdc
Maximum Junction Temperature	T_{Jmax}	150	°C
Power Dissipation, $T_A = 75^\circ\text{C}^*$ Derate linearly above 75°C @	$P_{D(max)}$	0.268 3.57	W mW/°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Storage Temperature	T_{stg}	-55 to +150	°C
Thermal Resistance Junction to Case*	$R_{\theta JC}$	280	°C/W

* Package mounted on 99.5% alumina $10 \times 8 \times 0.6$ mm.

DEVICE MARKING

MMBR920LT1, T3 = 7B

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 1.0$ mAdc, $I_E = 0$)	$V_{(BR)CEO}$	15	—	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 0.1$ mAdc, $I_E = 0$)	$V_{(BR)CBO}$	20	—	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 0.1$ mAdc, $I_C = 0$)	$V_{(BR)EBO}$	2.0	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 10$ Vdc, $I_E = 0$)	I_{CBO}	—	—	50	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 14$ mAdc, $V_{CE} = 10$ Vdc)	h_{FE}	25	—	250	—
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SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 14$ mAdc, $V_{CE} = 10$ Vdc, $f = 0.5$ GHz)	f_T	—	4.5	—	GHz
Collector-Base Capacitance ($V_{CB} = 10$ Vdc, $I_E = 0$, $f = 1.0$ MHz)	C_{cb}	—	—	1.0	pF
Noise Figure ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 0.5$ GHz) ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ GHz)	NF	—	2.4 3.0	—	dB
Common-Emitter Amplifier Power Gain ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 0.5$ GHz) ($I_C = 2.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ GHz)	G_{pe}	—	15 10	—	dB

REV 6

MMBR920LT1, T3

RF AMPLIFIER
TRANSISTOR
NPN SILICON



CASE 318-07, STYLE 6
SOT-23
LOW PROFILE